

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

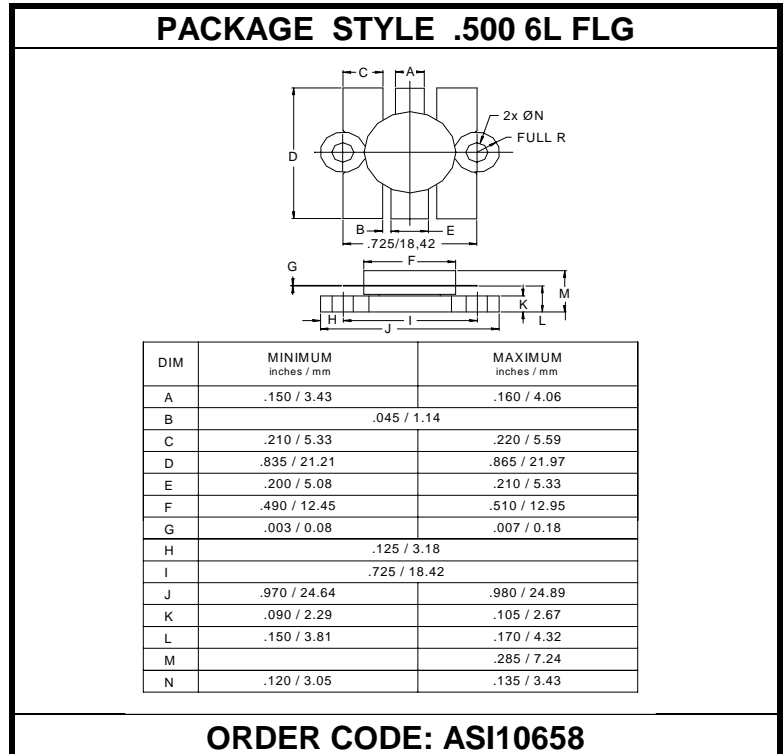
The **ASI TVV014A** is designed for Television Band III Applications up to 225 MHz.

FEATURES:

- Common Emitter
- $P_G = 14$ dB at 14 W/225 MHz
- **Omnigold™** Metalization System
- Emitter Ballasting

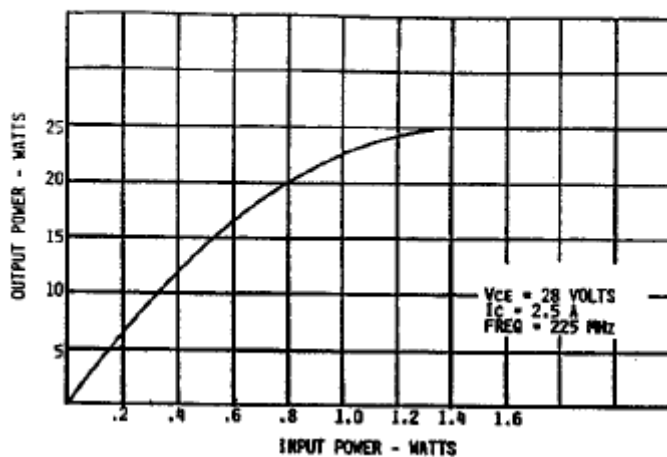
MAXIMUM RATINGS

I_C	10 A
V_{CBO}	60 V
V_{CEO}	35 V
V_{EBO}	4.0 V
P_{DISS}	140 W @ $T_C = 25^\circ\text{C}$
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	1.5 °C/W


CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 50$ mA	35			V
BV_{CER}	$I_C = 50$ mA $R_{BE} = 10 \Omega$	60			V
BV_{EBO}	$I_E = 10$ mA	4.0			V
I_{CES}	$V_{CE} = 50$ V			5.0	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 1.0$ A	10		100	---
C_{OB}	$V_{EB} = 28$ V $f = 1.0$ MHz			80	pF
P_G IMD_1	$V_{CE} = 28$ V $I_C = 2.5$ A $f = 225$ MHz $P_{OUT} = 14$ W	14		-55	dB dBc

POWER OUTPUT vs POWER INPUT



IMD vs POWER OUTPUT

